

HUF75332P3-VB Datasheet N-Channel 60-V (D-S) MOSFET

PRODUCT	ODUCT SUMMARY			
V _{DS} (V)	$R_{DS(on)}(\Omega)$	I _D (A) ^a		
60	0.011 at V _{GS} = 10 V	60		
00	0.013 at V _{GS} = 4.5 V	50		

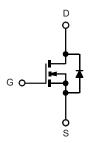
FEATURES

- 175 °C Junction Temperature
- · Trench Power MOSFET
- Material categorization:









N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS (T _C = 2	25 °C, unless other	wise noted)			
Parameter		Symbol	Limit	Unit	
Gate-Source Voltage		V _{GS}	± 20	V	
Continuous Dusin Coment /T = 475 °C\h	T _C = 25 °C		60		
Continuous Drain Current (T _J = 175 °C) ^b	T _C = 100 °C	l _D	50 ^a		
Pulsed Drain Current		I _{DM}	200	A	
Continuous Source Current (Diode Conduction)		I _S	50ª		
Avalanche Current		I _{AS}	50		
Single Avalanche Energy (Duty Cycle ≤ 1 %)	L = 0.1 mH	E _{AS}	125	mJ	
Mayimum Dayar Dissinction	T _C = 25 °C	Pn	136	W	
Maximum Power Dissipation	T _A = 25 °C		3 ^b , 8.3 ^{b, c}] vv	
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to 175	°C	

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typical	Maximum	Unit
Marrian una lun atian ta Analianta	t ≤ 10 sec	P	15	18	
Maximum Junction-to-Ambient ^a	Steady State	R_{thJA}	40	50	0 °C/W
Maximum Junction-to-Case		R _{thJC}	0.85	1.1	

Notes:

- a. Package limited.
- b. Surface mounted on 1" x 1" FR4 board.
- $c.\ t \leq 10\ s.$



Parameter	Symbol	Test Conditions	Min.	Typ.a	Max.	Unit
Static						
Drain-Source Breakdown Voltage	V _{DS}	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$	60			V
Gate Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	1		3	V
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			± 100	nA
		V _{DS} = 60 V, V _{GS} = 0 V			1	μA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 60 V, V _{GS} = 0 V, T _J = 125 °C			50	
		V _{DS} = 60 V, V _{GS} = 0 V, T _J = 175 °C			250	
On-State Drain Current ^b	I _{D(on)}	V _{DS} = 5 V, V _{GS} = 10 V	60			Α
		V _{GS} = 10 V, I _D = 20 A		0.011		
	D	V _{GS} = 10 V, I _D = 20 A, T _J = 125 °C		0.014		Ω
Drain-Source On-State Resistance ^b	R _{DS(on)}	V _{GS} = 10 V, I _D = 20 A, T _J = 175 °C		0.018		
		V _{GS} = 4.5 V, I _D = 15 A		0.013		
Forward Transconductance ^b	9 _{fs}	V _{DS} = 15 V, I _D = 20 A		60		S
Dynamic						
Input Capacitance	C _{iss}			4200		
Output Capacitance	C _{oss}	$V_{GS} = 0 \text{ V}, V_{DS} = 25 \text{ V}, f = 1 \text{ MHz}$		570		
Reverse Transfer Capacitance	C _{rss}			325		
Total Gate Charge ^c	Qg			47		
Gate-Source Charge ^c	Q _{gs}	$V_{DS} = 30 \text{ V}, V_{GS} = 10 \text{ V}, I_{D} = 50 \text{ A}$		10		nC
Gate-Drain Charge ^c	Q_{gd}			12		
Turn-On Delay Time ^c	t _{d(on)}			10	20	
Rise Time ^c	t _r	$V_{DD} = 30 \text{ V}, R_{L} = 0.6 \Omega$		15	25	no
Turn-Off Delay Time ^c	t _{d(off)}	$I_D \cong 50 \text{ A}, V_{GEN} = 10 \text{ V}, R_g = 2.5 \Omega$		35	50	- ns
Fall Time ^c	t _f			20	30	
Source-Drain Diode Ratings and Cha	aracteristics (T _C = 25 °C)				
Pulsed Current	I _{SM}				60	Α
Diode Forward Voltage	V _{SD}	I _F = 20 A, V _{GS} = 0 V		1	1.5	V
Reverse Recovery Time	t _{rr}	I _F = 20 A, di/dt = 100 A/μs		45	100	ns

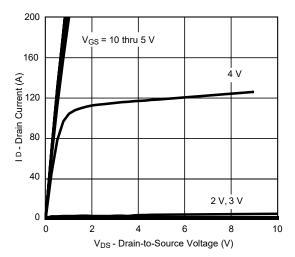
Notes:

- a. For design aid only; not subject to production testing.
- b. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %.
- c. Independent of operating temperature.

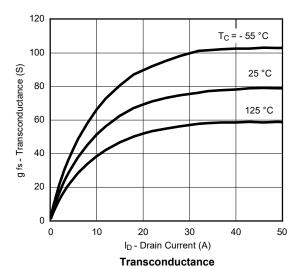
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



TYPICAL CHARACTERISTICS (25 °C unless noted)



Output Characteristics



2- Capacitance (pF) 3000 2400 1800 1300 1200 $\mathsf{C}_{\mathsf{oss}}$ 600 $\mathsf{C}_{\mathsf{rss}}$

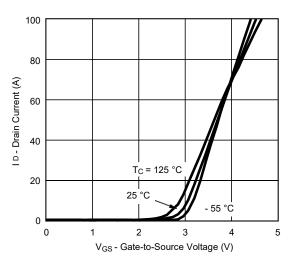
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C_{iss}

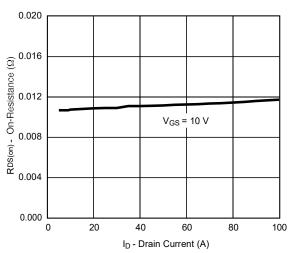
V_{DS} - Drain-to-Source Voltage (V) Capacitance

30

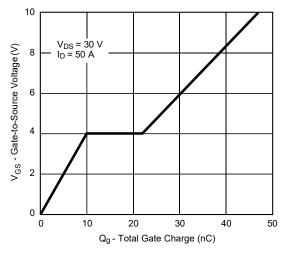
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Transfer Characteristics



On-Resistance vs. Drain Current



Gate Charge

4800 4200

3600

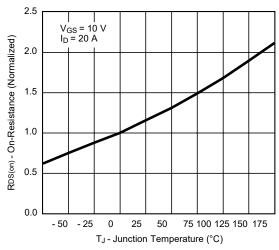
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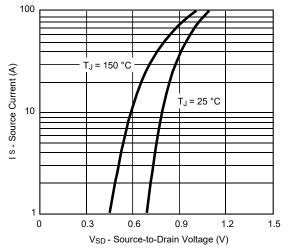
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TYPICAL CHARACTERISTICS (25 °C unless noted)



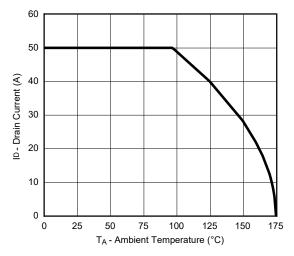
On-Resistance vs. Junction Temperature

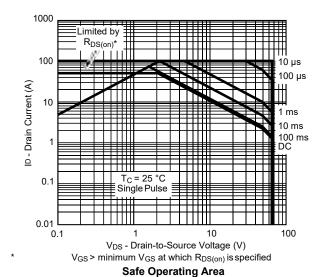


Source-Drain Diode Forward Voltage

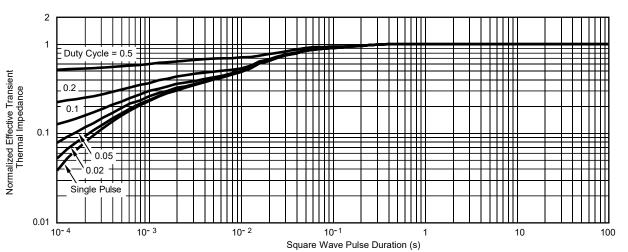


THERMAL RATINGS





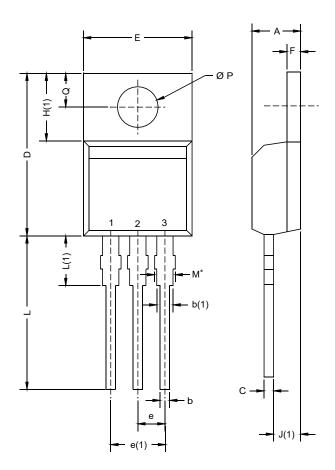
Maximum Drain Current vs. Ambient Temperature



Normalized Thermal Transient Impedance, Junction-to-Case



TO-220AB



DIM.	MILLIN	IETERS	INCHES		
	MIN.	MAX.	MIN.	MAX.	
Α	4.24	4.65	0.167	0.183	
b	0.69	1.02	0.027	0.040	
b(1)	1.14	1.78	0.045	0.070	
С	0.36	0.61	0.014	0.024	
D	14.33	15.85	0.564	0.624	
E	9.96	10.52	0.392	0.414	
е	2.41	2.67	0.095	0.105	
e(1)	4.88	5.28	0.192	0.208	
F	1.14	1.40	0.045	0.055	
H(1)	6.10	6.71	0.240	0.264	
J(1)	2.41	2.92	0.095	0.115	
L	13.36	14.40	0.526	0.567	
L(1)	3.33	4.04	0.131	0.159	
ØР	3.53	3.94	0.139	0.155	
Q	2.54	3.00	0.100	0.118	

Note

• M* = 0.052 inches to 0.064 inches (dimension including protrusion), heatsink hole for HVM



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